

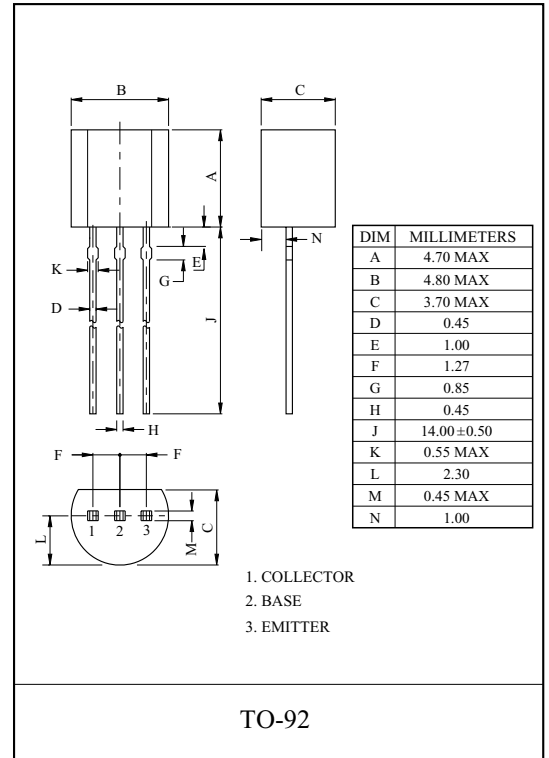
LOW NOISE APPLICATION.

#### FEATURE

- For Complementary with NPN Type BC549/550.

#### MAXIMUM RATING (Ta=25 )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	BC559	-30	V
	BC560	-50	
Collector-Emitter Voltage	BC559	-30	V
	BC560	-45	
Emitter-Base Voltage	V <sub>EBO</sub>	-5	V
Collector Current	I <sub>C</sub>	-100	mA
Collector Power Dissipation	P <sub>C</sub>	625	mW
Junction Temperature	T <sub>j</sub>	150	
Storage Temperature Range	T <sub>stg</sub>	-55 150	



#### ELECTRICAL CHARACTERISTICS (Ta=25 )

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Emitter Breakdown Voltage	BC559	I <sub>C</sub> =-10mA, I <sub>B</sub> =0	-30	-	-	V
	BC560		-45	-	-	
Collector-Base Breakdown Voltage	BC559	I <sub>C</sub> =-10 μA, I <sub>E</sub> =0	-30	-	-	V
	BC560		-50	-	-	
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-10 μA, I <sub>C</sub> =0	-5.0	-	-	V
Collector Cut-off Current	I <sub>CB0</sub>	V <sub>CB</sub> =-30V, I <sub>E</sub> =0	-	-	-15	nA
DC Current Gain	h <sub>FE</sub>	I <sub>C</sub> =-2mA, V <sub>CE</sub> =-5V	110	-	800	
Base-Emitter Voltage	V <sub>BE(ON)</sub>	I <sub>C</sub> =-2mA, V <sub>CE</sub> =-5V	-0.55	-	-0.7	V
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-100mA, I <sub>B</sub> =-5mA	-	-	-0.6	V
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-100mA, I <sub>B</sub> =-5mA	-	-0.9	-	V
Transition Frequency	f <sub>T</sub>	I <sub>C</sub> =-10mA, V <sub>CE</sub> =-5V, f=100MHz	-	300	-	MHz
Collector Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-10V, I <sub>E</sub> =0, f=1MHz	-	-	7.0	pF
Noise Figure	NF	I <sub>C</sub> =-200 μA, V <sub>CE</sub> =-5V R <sub>g</sub> =10k, f=1kHz	-	-	4.0	dB

Note : h<sub>FE</sub> Classification A:110 220, B:200 450, C:420 800